

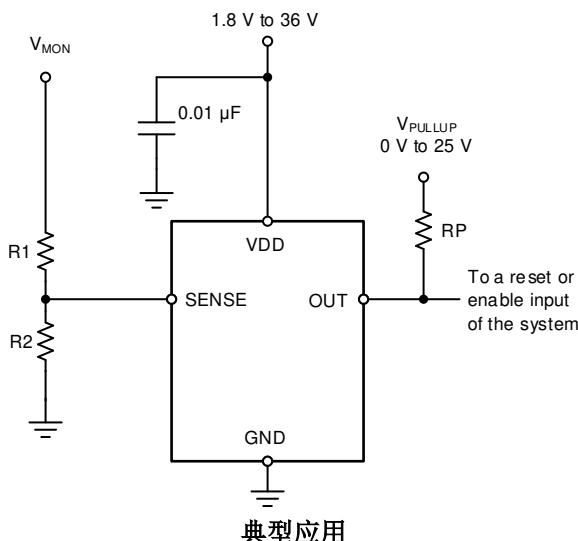
TPS3711 36V 电压检测器

1 特性

- 宽电源电压范围：1.8 V 至 36 V
- 可调节阈值：低至 400mV
- 开漏输出提供欠压保护
- 低静态电流：7 μ A (典型值)
- 高阈值精度：
 - 0.75% 过热
 - 0.25% (典型值)
- 内部迟滞：5.5 mV (典型值)
- 温度范围：-40°C 至 +125°C
- 封装：SOT-6

2 应用

- 工业控制系统
- 嵌入式计算模块
- DSP、微控制器和微处理器
- 笔记本电脑和台式机
- 便携式和电池供电类产品
- FPGA 和 ASIC 系统



3 说明

TPS3711 宽电源电压比较器在 1.8V 至 36V 的电压范围内运行。该器件具有一个内部基准电压为 400mV 的精密比较器以及一个额定电压为 25V 的开漏输出，用于实现欠压检测。监视电压可使用外部电阻进行设置。

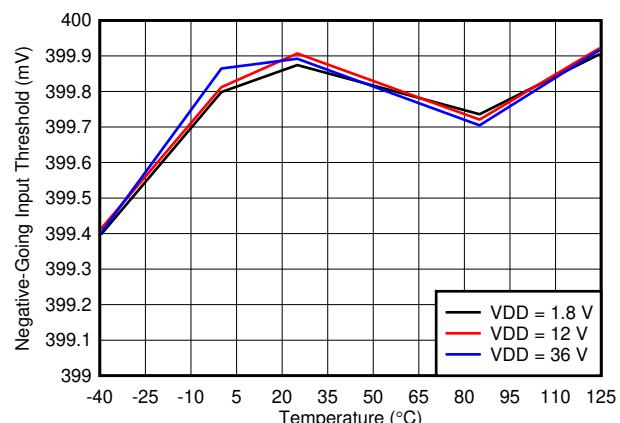
当 SENSE 引脚的电压降至负向阈值以下时，OUT 被驱动为低电平；当 SENSE 引脚的电压升至正向阈值以上时，OUT 被驱动为高电平。TPS3711 的比较器内置实现噪声抑制的滞后特性，可避免触发错误，从而确保输出稳定运行。

TPS3711 采用 SOT-6 封装，额定工作结温范围为 -40°C 至 +125°C。

器件信息

器件型号	封装 (1)	封装尺寸 (标称值)
TPS3711	SOT (6)	2.90mm x 1.60mm

(1) 要了解所有可用封装，请见数据表末尾的封装选项附录。

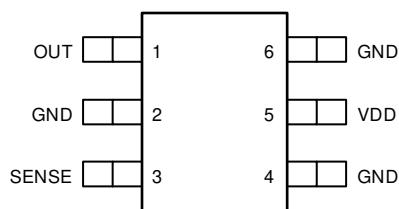


本资源的原文使用英文撰写。为方便起见，TI 提供了译文；由于翻译过程中可能使用了自动化工具，TI 不保证译文的准确性。为确认准确性，请务必访问 ti.com 参考最新的英文版本（控制文档）。

Table of Contents

1 特性	1	6.4 Device Functional Modes.....	11
2 应用	1	7 Application and Implementation	12
3 说明	1	7.1 Application Information.....	12
4 Pin Configuration and Functions	3	7.2 Typical Application.....	13
5 Specifications	4	7.3 Power Supply Recommendations.....	14
5.1 Absolute Maximum Ratings ⁽¹⁾	4	7.4 Layout.....	15
5.2 ESD Ratings.....	4	8 Device and Documentation Support	16
5.3 Recommended Operating Conditions.....	4	8.1 Documentation Support.....	16
5.4 Thermal Information.....	4	8.2 支持资源.....	16
5.5 Electrical Characteristics.....	5	8.3 Trademarks.....	16
5.6 Timing Requirements.....	6	8.4 静电放电警告.....	16
5.7 Typical Characteristics.....	7	8.5 术语表.....	16
6 Detailed Description	10	9 Revision History	16
6.1 Overview.....	10	10 Mechanical, Packaging, and Orderable Information	16
6.2 Functional Block Diagram.....	10		
6.3 Feature Description.....	11		

4 Pin Configuration and Functions



**图 4-1. DDC Package
6-Pin SOT
Top View**

表 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
GND	2, 4, 6	—	Ground. Connect all three pins to ground.
OUT	1	O	Comparator open-drain output. This pin is driven low when the voltage at this comparator is less than V_{IT^-} . The output goes high when the sense voltage rises above V_{IT^+} .
SENSE	3	I	Comparator input. This pin is connected to the voltage to be monitored with the use of an external resistor divider. When the voltage at this pin drops below the threshold voltage V_{IT^-} , OUT is driven low.
VDD	5	I	Supply-voltage input. Connect a 1.8-V to 36-V supply to VDD to power the device. It is good analog design practice to place a 0.1- μ F ceramic capacitor close to this pin.

5 Specifications

5.1 Absolute Maximum Ratings ⁽¹⁾

over operating junction temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Voltage ⁽²⁾	V _{DD}	- 0.3	40	V
	V _{OUT}	- 0.3	28	
	V _{SENSE}	- 0.3	7	
Current	Output pin current		40	mA
Temperature	Operating junction, T _J	- 40	125	°C
	Storage, T _{stg}	- 55	125	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltages are with respect to network ground terminal.

5.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{DD}	Supply pin voltage	1.8	36	V	
V _{SENSE}	Input pin voltage	0	6.5 ⁽¹⁾	V	
V _{OUT}	Output pin voltage	0	25	V	
V _{PULLUP}	Pullup voltage	0	25	V	
I _{OUT}	Output pin current	0	10	mA	
T _J	Junction temperature	- 40	25	125	°C

- (1) Operating V_{sense} at 1.7 V or higher and at 125°C continuously for 10 years or more would cause a degradation of accuracy spec to 1.5% maximum.

5.4 Thermal Information

THERMAL METRIC	TPS3711	UNIT	
	DDC (SOT)		
	6 PINS		
R _{θ JA}	Junction-to-ambient thermal resistance	201.6	°C/W
R _{θ JC(top)}	Junction-to-case (top) thermal resistance	47.8	°C/W
R _{θ JB}	Junction-to-board thermal resistance	51.2	°C/W
ψ _{JT}	Junction-to-top characterization parameter	0.7	°C/W
ψ _{JB}	Junction-to-board characterization parameter	50.8	°C/W
R _{θ JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

5.5 Electrical Characteristics

Over the operating temperature range of $T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$, $1.8 \text{ V} \leq V_{\text{DD}} < 36 \text{ V}$, and pullup resistor $R_P = 100 \text{ k}\Omega$ (unless otherwise noted). Typical values are at $T_J = 25^{\circ}\text{C}$ and $V_{\text{DD}} = 12 \text{ V}$.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(\text{POR})}$	Power-on reset voltage ⁽¹⁾			0.8	V
$V_{(\text{IT}-)}$	SENSE pin negative input threshold voltage	$V_{\text{DD}} = 1.8 \text{ V to } 36 \text{ V}$	397	400	403
$V_{(\text{IT}+)}$	SENSE pin positive input threshold voltage	$V_{\text{DD}} = 1.8 \text{ V to } 36 \text{ V}$	400	405.5	413
$V_{(\text{HYS})}$	SENSE pin hysteresis voltage ($\text{HYS} = V_{(\text{IT}+)} - V_{(\text{IT}-)}$)		2	5.5	12
$V_{(\text{OL})}$	Low-level output voltage	$V_{\text{DD}} = 1.8 \text{ V}, I_{\text{OUT}} = 3 \text{ mA}$		130	250
		$V_{\text{DD}} = 5 \text{ V}, I_{\text{OUT}} = 5 \text{ mA}$		150	250
$I_{(\text{IN})}$	Input current (at SENSE pin)	$V_{\text{DD}} = 1.8 \text{ V and } 36 \text{ V}, V_{\text{SENSE}} = 6.5 \text{ V}$	-25	+1	+25
		$V_{\text{DD}} = 1.8 \text{ V and } 36 \text{ V}, V_{\text{SENSE}} = 0.1 \text{ V}$	-15	+1	+15
$I_{(\text{D leak})}$	Open-drain leakage current	$V_{\text{DD}} = 1.8 \text{ V and } 36 \text{ V}, V_{\text{OUT}} = 25 \text{ V}$		10	300
$I_{(\text{DD})}$	Supply current	$V_{\text{DD}} = 1.8 \text{ V} - 36 \text{ V}$		8	11
UVLO	Undervoltage lockout ⁽²⁾	V_{DD} falling	1.3	1.5	1.7

(1) The lowest supply voltage (V_{DD}) at which output is active; $t_{(\text{VDD})} > 15 \mu\text{s}/\text{V}$. If less than $V_{(\text{POR})}$, the output is undetermined.

(2) When V_{DD} falls below UVLO, OUT is driven low. The output cannot be determined if less than $V_{(\text{POR})}$.

5.6 Timing Requirements

PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT
$t_{pd(HL)}$	High-to-low propagation delay ⁽¹⁾ $V_{DD} = 24 \text{ V}, \pm 10\text{-mV}$ input overdrive, $R_L = 100 \text{ k}\Omega, V_{OH} = 0.9 \times V_{DD}, V_{OL} = 250 \text{ mV}$		9.9		μs
$t_{pd(LH)}$	Low-to-high propagation delay ⁽¹⁾ $V_{DD} = 24 \text{ V}, \pm 10\text{-mV}$ input overdrive, $R_L = 100 \text{ k}\Omega, V_{OH} = 0.9 \times V_{DD}, V_{OL} = 250 \text{ mV}$		28.1		μs
$t_{d(start)}$ ⁽²⁾	Startup delay $V_{DD} = 5 \text{ V}$		155		μs
t_r	Output rise time $V_{DD} = 12 \text{ V}, 10\text{-mV}$ input overdrive, $R_L = 100 \text{ k}\Omega, C_L = 10 \text{ pF}, V_O = (0.1 \text{ to } 0.9) \times V_{DD}$		2.7		μs
t_f	Output fall time $V_{DD} = 12 \text{ V}, 10\text{-mV}$ input overdrive, $R_L = 100 \text{ k}\Omega, C_L = 10 \text{ pF}, V_O = (0.9 \text{ to } 0.1) \times V_{DD}$		0.12		μs

(1) High-to-low and low-to-high refers to the transition at the input pin (SENSE).

(2) During power on, V_{DD} must exceed 1.8 V for at least 150 μs (typ) before the output state reflects the input condition.

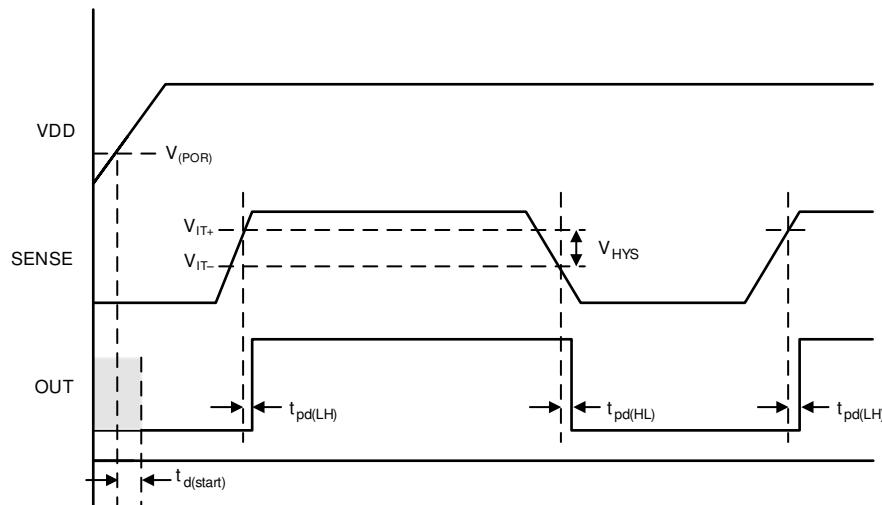


图 5-1. Timing Diagram

5.7 Typical Characteristics

at $T_J = 25^\circ\text{C}$ and $V_{DD} = 12\text{ V}$ (unless otherwise noted)

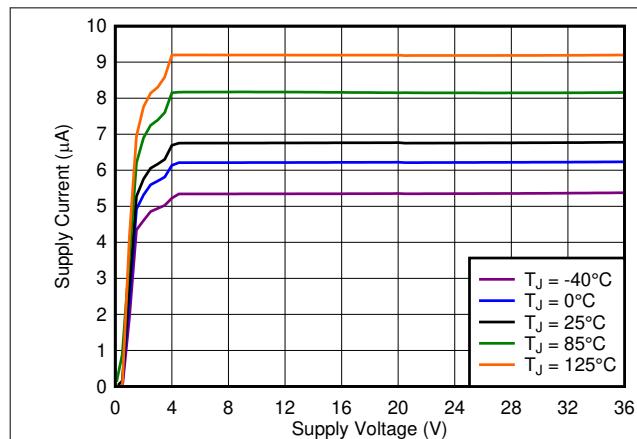
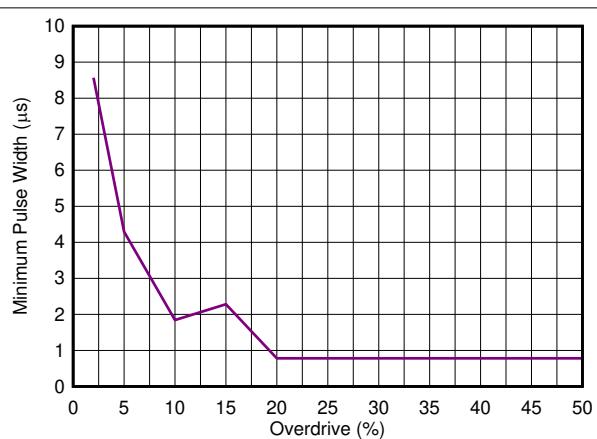


图 5-2. Supply Current vs Supply Voltage



$V_{DD} = 24\text{ V}$, minimum pulse duration required to trigger output high-to-low transition, SENSE = negative spike below V_{IT^-}

图 5-3. Minimum Pulse Duration vs Threshold Overdrive Voltage

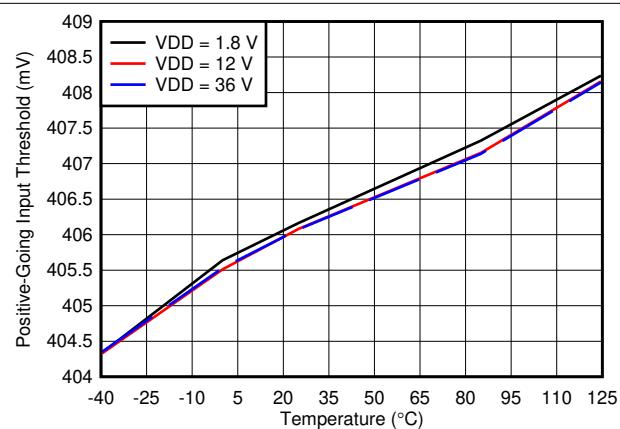


图 5-4. SENSE Positive Input Threshold Voltage (V_{IT^+}) vs Temperature

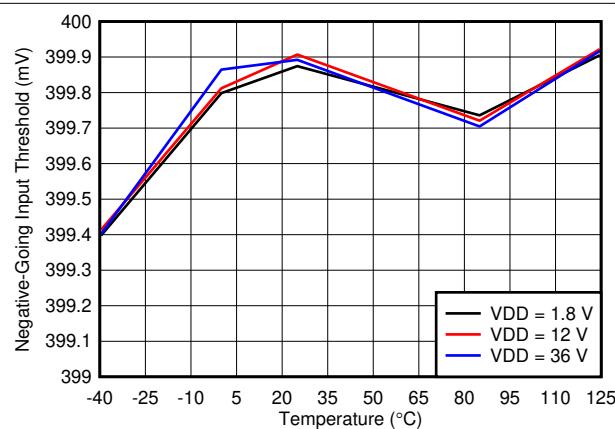


图 5-5. SENSE Negative Input Threshold Voltage (V_{IT^-}) vs Temperature

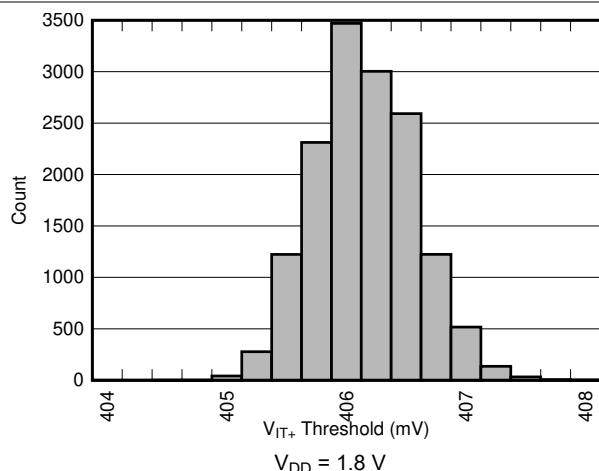


图 5-6. SENSE Positive Input Threshold Voltage (V_{IT+}) Distribution

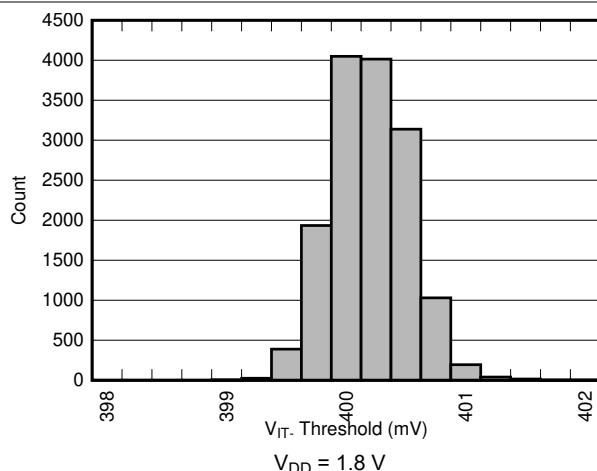


图 5-7. SENSE Negative Input Threshold Voltage (V_{IT-}) Distribution

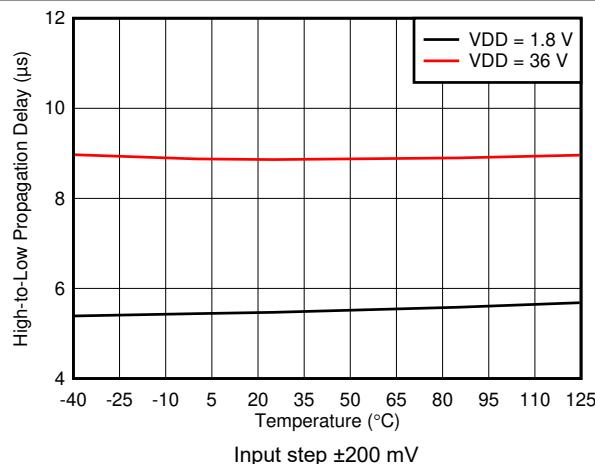


图 5-8. Propagation Delay vs Temperature (High-to-Low Transition at SENSE)

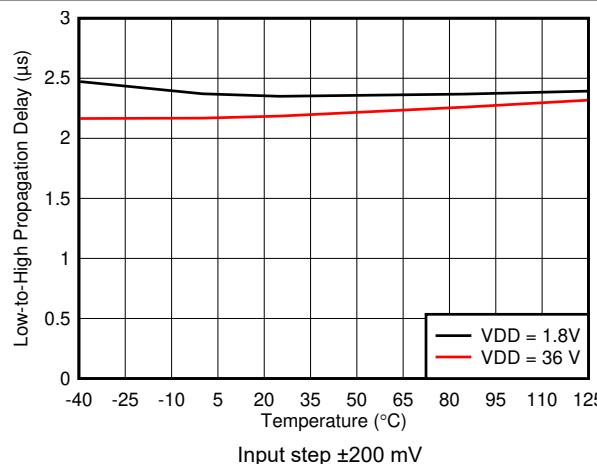


图 5-9. Propagation Delay vs Temperature (Low-to-High Transition at SENSE)

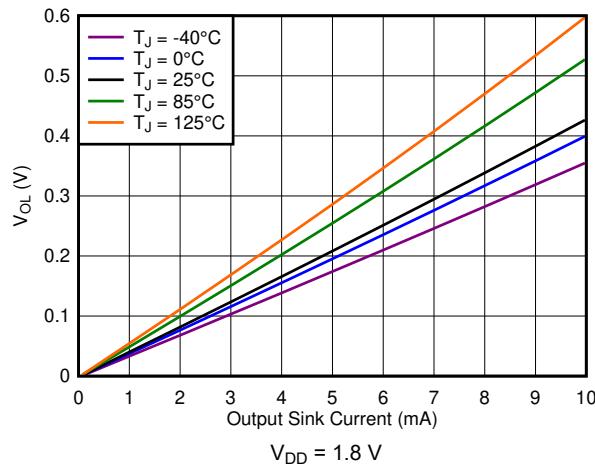


图 5-10. Output Voltage Low vs Output Sink Current

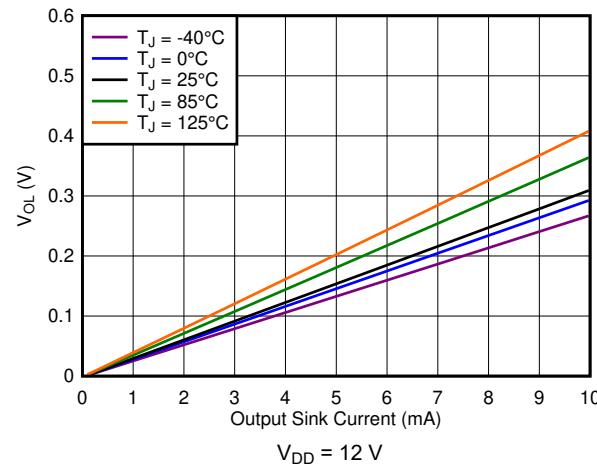


图 5-11. Output Voltage Low vs Output Sink Current

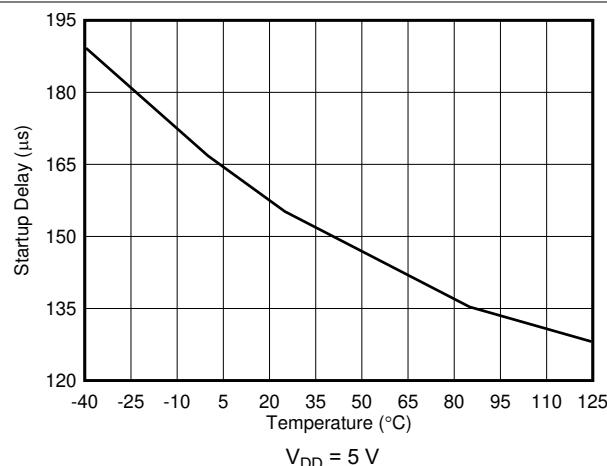


图 5-12. Startup Delay vs Temperature

6 Detailed Description

6.1 Overview

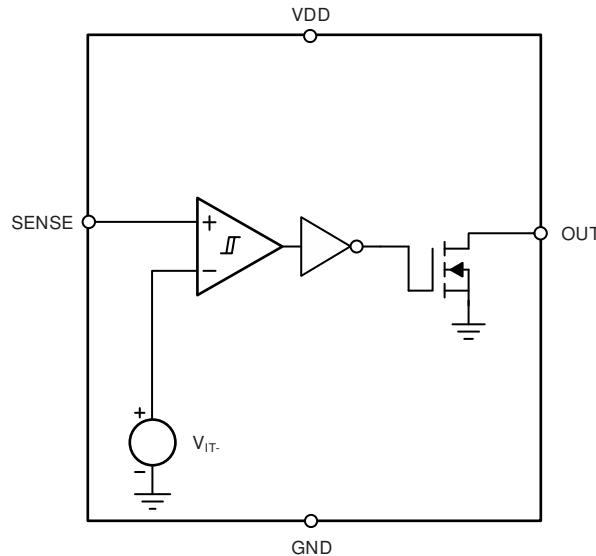
The TPS3711 combines a comparator and a precision reference for undervoltage detection. The TPS3711 features a wide supply voltage range (1.8 V to 36 V) and a high-accuracy threshold voltage of 400 mV (0.75% overtemperature) with built-in hysteresis. The output is rated to 25 V and can sink up to 10 mA.

Set the input pin (SENSE) to monitor any voltage above 0.4 V by using an external resistor divider network. SENSE has very low input leakage current, allowing the use of a large resistor divider without sacrificing system accuracy. The relationship between the input and the output is shown in 表 6-1. Broad voltage thresholds are supported that enable the device to be used in a wide array of applications.

表 6-1. Truth Table

CONDITION	OUTPUT	STATUS
SENSE > V_{IT+}	OUT high	Output high impedance
SENSE < V_{IT-}	OUT low	Output asserted

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Input Pin (SENSE)

The TPS3711 combines a comparator with a precision reference voltage. The comparator has one external input and one internal input connected to the internal reference. The falling threshold on SENSE is designed and trimmed to be equal to the reference voltage (400 mV). This configuration optimizes the device accuracy. The comparator also has built-in hysteresis that proves immunity to noise and ensures stable operation.

The comparator input swings from ground to 6.5 V (7.0 V absolute maximum), regardless of the device supply voltage used. Although not required in most cases, it is good analog design practice to place a 1-nF to 10-nF bypass capacitor at the comparator input for noisy applications in order to reduce sensitivity to transient voltage changes on the monitored signal.

For the comparator, the output (OUT) is driven to logic low when the input SENSE voltage drops below V_{IT^-} . When the voltage exceeds V_{IT^+} , OUT goes to a high-impedance state; see [图 5-1](#).

6.3.2 Output Pin (OUT)

In a typical TPS3711 application, the output is connected to a reset or enable input of the processor [such as a digital signal processor (DSP), application-specific integrated circuit (ASIC), or other processor type] or the output is connected to the enable input of a voltage regulator [such as a dc-dc converter or low-dropout regulator (LDO)].

The TPS3711 provides an open-drain output (OUT); use a pullup resistor to hold the line high when the output goes to a high-impedance state. Connect this pullup resistor to a voltage rail that meets the logic requirements of the downstream device. The TPS3711 output can be pulled up to 25 V, independent of the device supply voltage. To make sure the proper voltage level, give some consideration when choosing the pullup resistor value. The pullup resistor value is determined by V_{OL} , output capacitive loading, and the open-drain leakage current ($I_{D(\text{leak})}$). These values are specified in the [表 5.5](#) table.

[表 6-1](#) and the [节 6.3.1](#) section describe how the output is asserted or high impedance. See [图 5-1](#) for a timing diagram that describes the relationship between threshold voltage and the respective output.

6.4 Device Functional Modes

6.4.1 Normal Operation ($V_{DD} > UVLO$)

When the voltage on VDD is greater than 1.8 V for at least 155 μ s, the OUT signal corresponds to the voltage on SENSE, as listed in [表 6-1](#).

6.4.2 Undervoltage Lockout ($V_{(POR)} < V_{DD} < UVLO$)

When the voltage on VDD is less than the device UVLO voltage, and greater than the power-on reset voltage, $V_{(POR)}$, the OUT signal is asserted regardless of the voltage on SENSE.

6.4.3 Power On Reset ($V_{DD} < V_{(POR)}$)

When the voltage on VDD is lower than the required voltage to internally pull the asserted output to GND ($V_{(POR)}$), OUT is in a high-impedance state.

7 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

7.1 Application Information

The TPS3711 is used as a precision voltage supervisor in several different configurations. The monitored voltage (V_{MON}), VDD voltage, and output pullup voltage can be independent voltages or connected in any configuration. The following sections show the connection configurations and the voltage limitations for each configuration.

7.1.1 Input and Output Configurations

图 7-1 到 图 7-2 show examples of the various input and output configurations.

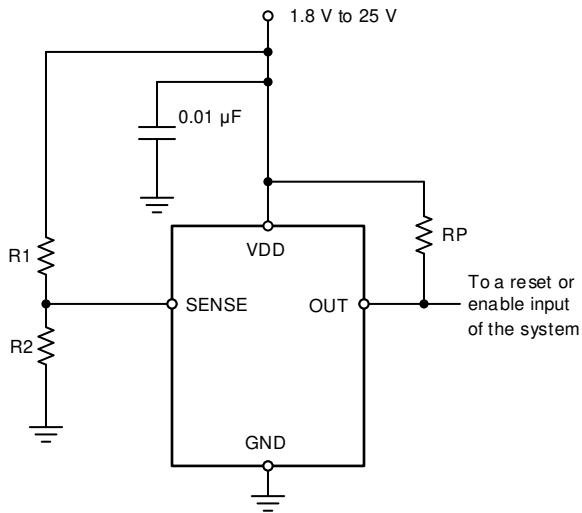
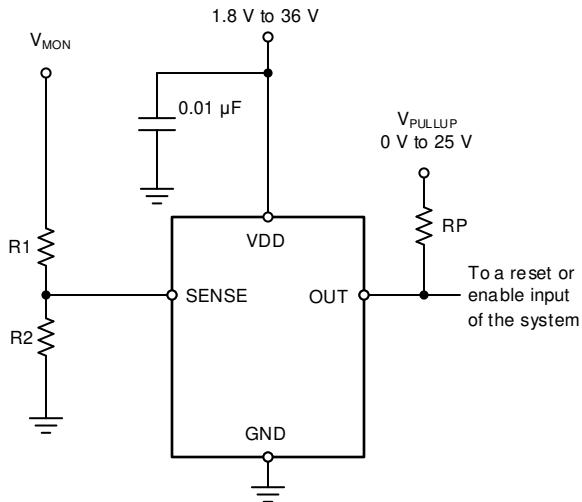


图 7-1. Monitoring the Same Voltage as V_{DD}



NOTE: The input can monitor a voltage higher than V_{DD} (max) with the use of an external resistor divider network.

图 7-2. Monitoring a Voltage Other than V_{DD}

7.1.2 Immunity to Input Pin Voltage Transients

The TPS3711 is immune to short voltage transient spikes on the input pin. Sensitivity to transients depends on both transient duration and amplitude; see [图 5-3, Minimum Pulse Duration vs Threshold Overdrive Voltage](#).

7.2 Typical Application

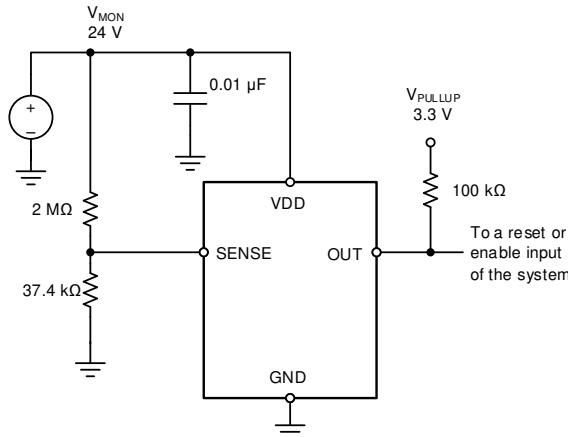


图 7-3. 24-V, 10% Comparator

7.2.1 Design Requirements

表 7-1. Design Parameters

PARAMETER	DESIGN REQUIREMENT	DESIGN RESULT
Monitored voltage	24-V nominal, falling ($V_{MON(UV)}$) threshold 10% nominal (21.6 V)	$V_{MON(UV)} = 21.8 \text{ V} \pm 2.7\%$
Output logic voltage	3.3-V CMOS	3.3-V CMOS
Maximum current consumption	30 μA	24 μA

7.2.2 Detailed Design Procedure

7.2.2.1 Resistor Divider Selection

The resistor divider values and target threshold voltage can be calculated by using [方程式 1](#) to determine $V_{MON(UV)}$.

$$V_{MON(UV)} = \left(1 + \frac{R_1}{R_2}\right) \times V_{IT-} \quad (1)$$

where

- R_1 and R_2 are the resistor values for the resistor divider on the SENSE pin
- $V_{MON(UV)}$ is the target voltage at which an undervoltage condition is detected

Choose an R_{TOTAL} (= $R_1 + R_2$) so that the current through the divider is approximately 100 times higher than the input current at the SENSE pin. Use resistors with high values to minimize current consumption (as a result of low input bias current) without adding significant error to the resistive divider. For details on sizing input resistors, refer to application report [SLVA450, Optimizing Resistor Dividers at a Comparator Input](#), available for download from www.ti.com.

7.2.2.2 Pullup Resistor Selection

To make sure the proper logic-high voltage level (V_{HI}), select a pullup resistor value where the pullup voltage divided by the pullup resistor value does not exceed the sink-current capability of the device. Confirm this voltage level by verifying that the pullup voltage minus the open-drain leakage current ($I_{D(\text{leak})}$) multiplied by the resistor is greater than the desired V_{HI} . These values are specified in the [节 5.5](#).

Use [方程式 2](#) to calculate the value of the pullup resistor.

$$\frac{V_{HI} - V_{\text{pullup}}}{I_{D(\text{leak})}} \leq R_P \leq \frac{V_{\text{pullup}}}{I_{\text{OUT}}} \quad (2)$$

7.2.2.3 Input Supply Capacitor

Although an input capacitor is not required for stability, for good analog design practice, connect a 0.1- μF low equivalent series resistance (ESR) capacitor across the VDD and GND pins. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is not located close to the power source.

7.2.3 Application Curves

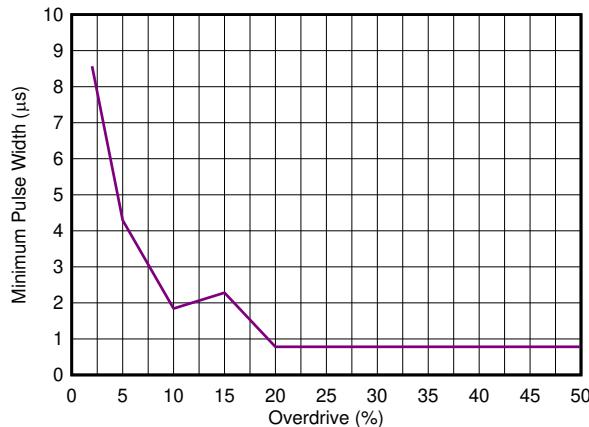


图 7-4. 24-V Window Monitor Output Response

7.3 Power Supply Recommendations

The TPS3711 has a 40-V absolute maximum rating on the VDD pin, with a recommended maximum operating condition of 36 V. If the voltage supply that provides power to VDD is susceptible to any large voltage transient that may exceed 40 V, or if the supply exhibits high voltage slew rates greater than 1 V/ μs , then place an RC filter between the supply and VDD to filter any high-frequency transient surges on the VDD pin. In these cases, a 100- Ω resistor and 0.01- μF capacitor are required, as shown in [图 7-5](#).

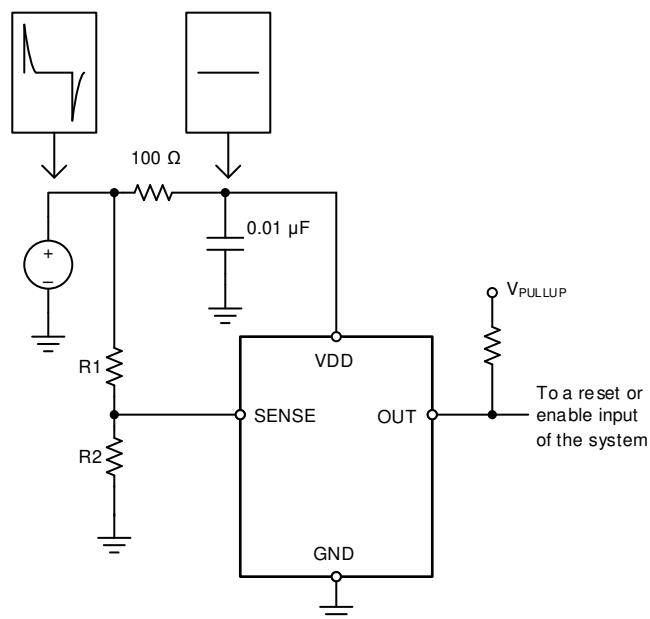


图 7-5. Using an RC Filter to Remove High-Frequency Disturbances on VDD

7.4 Layout

7.4.1 Layout Guidelines

- Place R_1 and R_2 close to the device to minimize noise coupling into the SENSE node.
- Place the VDD decoupling capacitor close to the device.
- Avoid using long traces for the VDD supply node. The VDD capacitor (C_{VDD}), along with parasitic inductance from the supply to the capacitor, might form an LC tank and create ringing with peak voltages above the maximum VDD voltage. If long traces are unavoidable, see 图 7-5 for an example of filtering VDD.

7.4.2 Layout Example

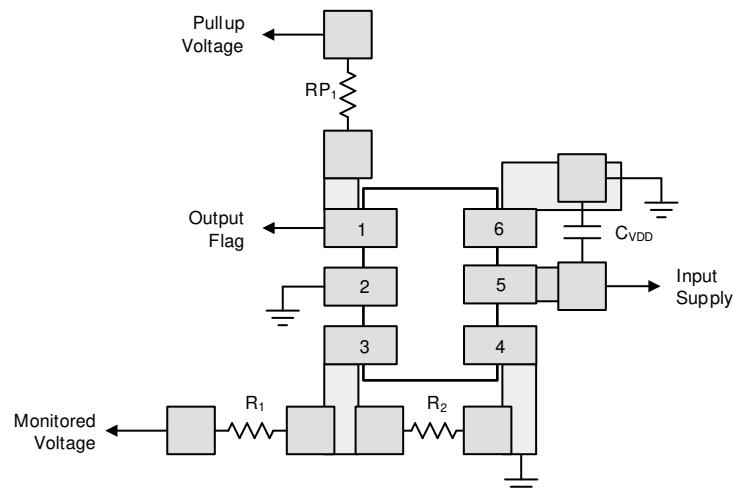


图 7-6. Recommended Layout

8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Documentation

For related documentation, see the following application report, available through the TI website at www.ti.com:

- *Optimizing Resistor Dividers at a Comparator Input*, [SLVA450](#)

8.2 支持资源

[TI E2E™ 中文支持论坛](#)是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的[使用条款](#)。

8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

8.4 静电放电警告

 静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.5 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

Changes from Revision A (November 2015) to Revision B (December 2023)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• Updated storage temperature range.....	4
<hr/>	
Changes from Revision * (November 2015) to Revision A ()	Page
• Changed input pin voltage maximum value from 1.7 V to 6.5 V.....	4
• Added tablenote	4

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS3711DDCR	ACTIVE	SOT-23-THIN	DDC	6	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	11BO	Samples
TPS3711DDCT	ACTIVE	SOT-23-THIN	DDC	6	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	11BO	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

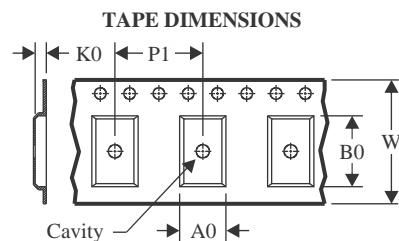
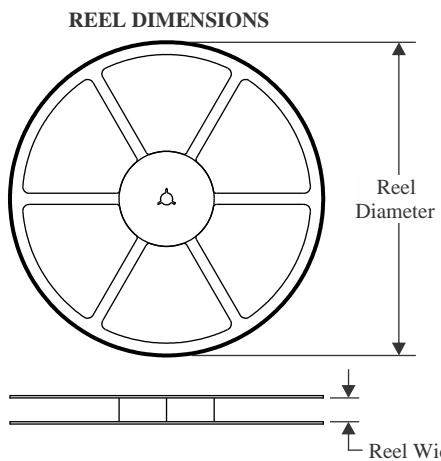
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

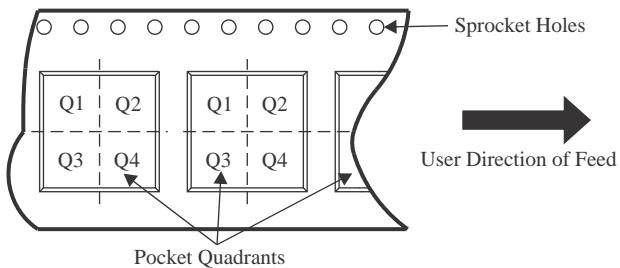
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION



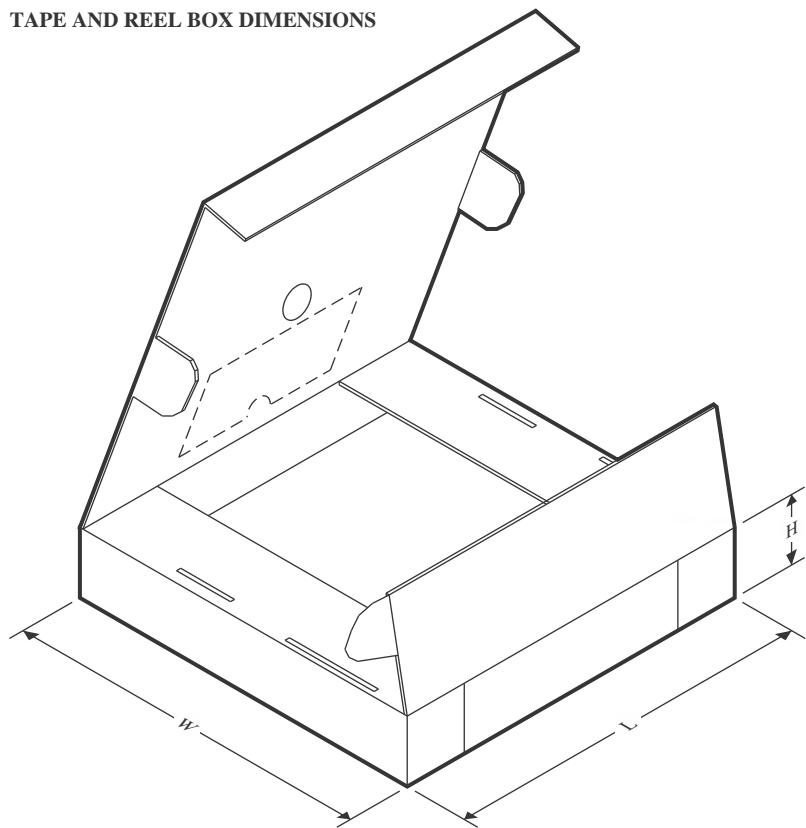
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS3711DDCR	SOT-23-THIN	DDC	6	3000	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
TPS3711DDCT	SOT-23-THIN	DDC	6	250	179.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS3711DDCR	SOT-23-THIN	DDC	6	3000	213.0	191.0	35.0
TPS3711DDCT	SOT-23-THIN	DDC	6	250	213.0	191.0	35.0

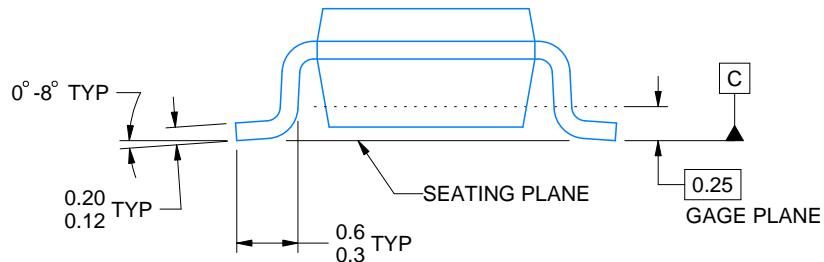
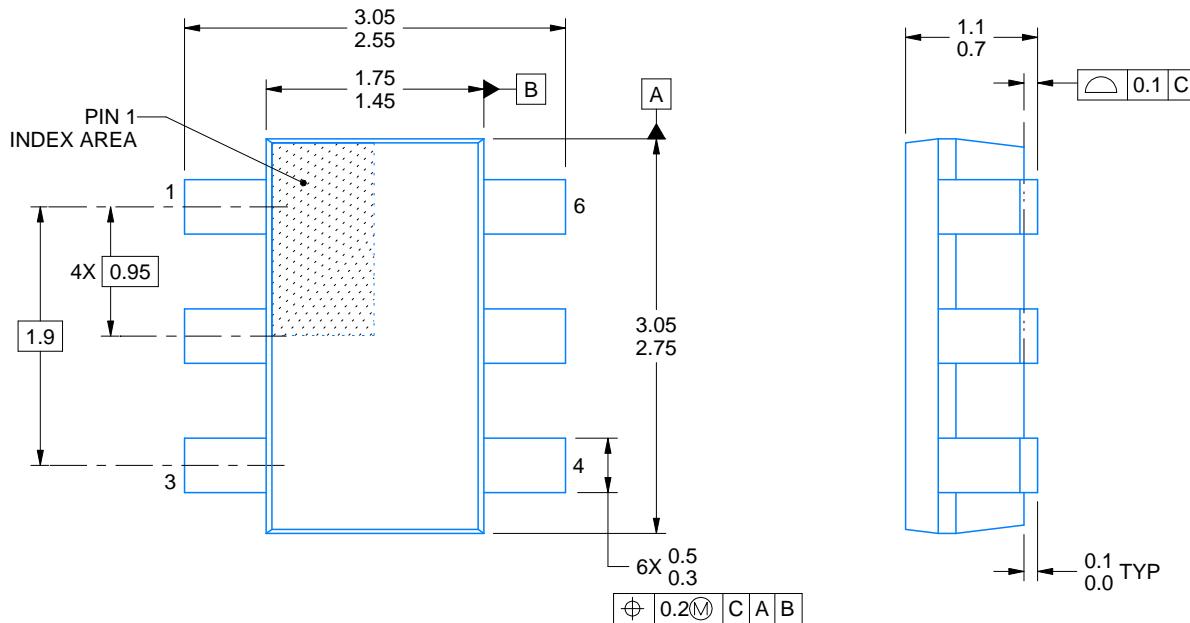
DDC0006A



PACKAGE OUTLINE

SOT-23 - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214841/C 04/2022

NOTES:

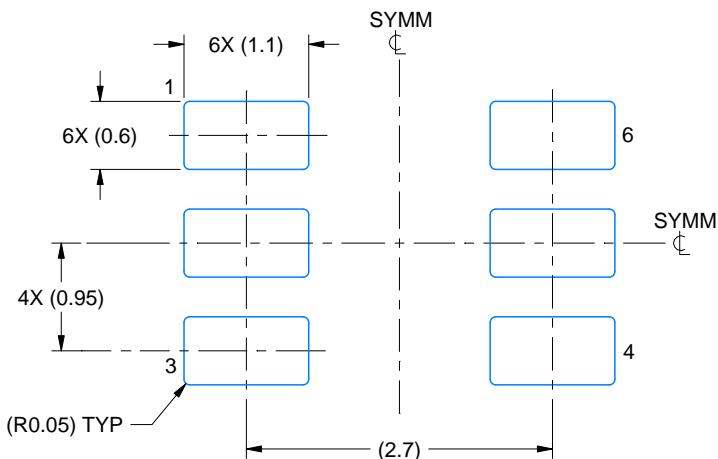
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-193.

EXAMPLE BOARD LAYOUT

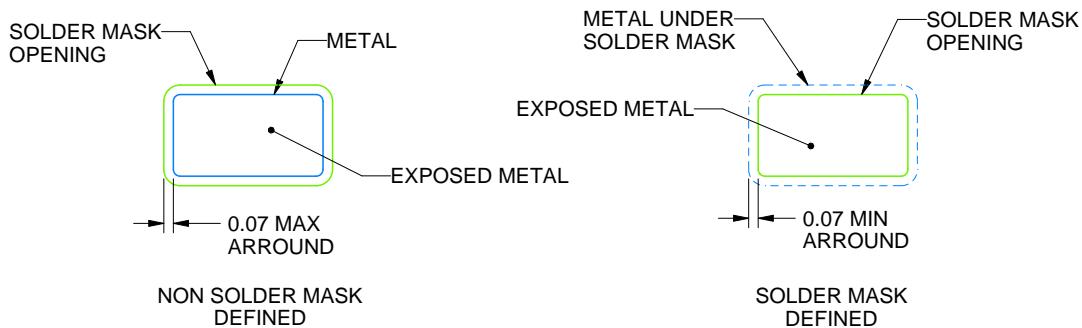
DDC0006A

SOT-23 - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPLODED METAL SHOWN
SCALE:15X



SOLDERMASK DETAILS

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NOTES: (continued)

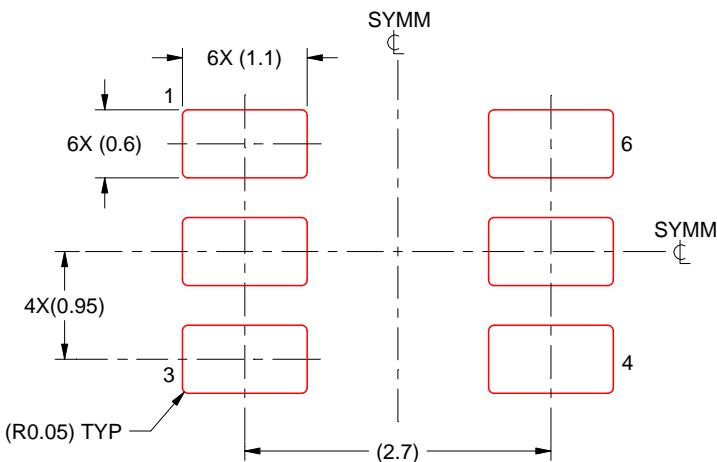
4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DDC0006A

SOT-23 - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:15X

4214841/C 04/2022

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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